

# Program

as of September 16, 2009

## **Saturday (September 26, 2009)**

16:00                      Registration start

19:00 – 23:00            Get-together party

# Sunday (September 27, 2009)

09:00 – 09:20          Opening

## Plenary Session

*Session chair: H. Grimmeiss*

- 09:20 – 10:10          **Electrical and optical properties of dislocations in Si**  
V. Kveder (*invited*)
- 10:10 – 11:00          **Dislocation nucleation in heteroepitaxial semiconducting films**  
B. Pichaud (*invited*), N. Burle, M. Texier, C. Fontaine and V. Vdovin
- 11:00 – 11:20          *COFFEE BREAK*
- 11:20 – 12:10          **Numerical analysis of mc-Si crystal growth**  
K. Kakimoto (*invited*), H. Matsuo, S. Hisamatsu, B. Ganesh, G. Bing, X.J. Chen, L. Liu, H. Miyazawa and Y. Kangawa
- 12:10 – 14:00          *LUNCH*

*Session chair: H. Richter*

- 14:00 – 14:50          **Trends in photovoltaics**  
P. Fath (*invited*)

## Session: Point Defects and Oxygen

- 14:50 – 15:10          **Properties of fast-diffusing oxygen species in silicon deduced from the generation kinetics of thermal donors**  
V.V. Voronkov, G.I. Voronkova, A.V. Batunina, V.N. Golovina, R. Falster, M. Cornara, N.B. Tiurina and A.S. Guliaeva
- 15:10 – 15:30          **Oxygen precipitation in conventional and nitrogen co-doped heavily arsenic-doped Czochralski silicon crystals: Ostwald ripening**  
X. Ma, Y. Feng, Y. Zeng and D. Yang
- 15:30 – 15:50          **The role of the interstitial oxygen in the recovery and evolution of the boron implantation damage**  
I. Mica, M.L. Polignano, F. Cazzaniga, L. Di Piazza, M. Mariani, E. Ricci, F. Sammiceli and S. Speranza
- 15:50 – 16:20          *COFFEE BREAK*

Session chair: A. Cavallini

- 16:20 – 17:00      **Review of stress effects on dopant solubility in Si and SiGe layers**  
N.S. Bennett, C. Ahn, N.E.B. Cowern and P. Pichler (*invited*)
- 17:00 – 17:20      **Rate equation modeling, ab initio calculation, and high sensitive FTIR investigations of the early stages of oxide precipitation in vacancy-rich CZ silicon**  
G. Kissinger, J. Dabrowski, V. Akhmetov, A. Sattler, D. Kot and W. von Ammon
- 17:20 – 17:40      **Low-temperature elastic softening due to vacancies in B-doped FZ Si crystals**  
H. Yamada-Kaneta, H. Watanabe, Y. Nagai, S. Baba, M. Akatsu, Y. Nemoto and T. Goto
- 17:40 – 18:00      **Oxygen diffusion in Si<sub>1-x</sub>Ge<sub>x</sub> alloys**  
L.I. Khirunencko, Y.V. Pomezov, M.G. Sosnin, A.V. Duvanskii, S.K. Golyk, N.V. Abrosimov and H. Riemann
- 18:00 – 19:30                      *DINNER*

## Poster Session 1

19:30 – open end

# Monday (September 28, 2009)

## Session: Photovoltaic Silicon and Defects

*Session chair: W. Koch*

- 08:30 – 09:10      **Influence of defects on solar cell characteristics**  
O. Breitenstein (*invited*), J. Bauer, P. P. Altermatt and K. Ramspeck
- 09:10 – 09:50      **Dislocation engineering in multi-crystalline silicon**  
M. Bertoni (*invited*), C. Colin and T. Bounassisi
- 09:50 – 10:10      **Analysis of heterogeneous iron precipitation in mc-Si**  
A. Haarahiltunen, V. Vähänissi, M. Yli-Koski, H. Talvitie and H. Savin
- 10:10 – 10:30      **Photovoltaic-quality silicon epitaxy by hot-wire CVD at glass-compatible temperatures**  
C.W. Teplin, I.T. Martin, M. Shub, R.C. Reedy, K.M. Jones, M.J. Romero, P. Stradins and H.M. Branz
- 10:30 – 10:50                      *COFFEE BREAK*

*Session chair: E. Weber*

- 10:50 – 11:30      **Multi-crystalline Si wafers for solar cells**  
Y. Wan (*invited*)
- 11:30 – 12:10      **Conduction mechanisms in doped and undoped nc-Si for PV**  
A. Cavallini (*invited*)
- 12:10 – 14:00                      *LUNCH*

## Session: Hydrogen and Defect Passivation in Si

*Session chair: T. Buonassisi*

- 14:00 – 14:40      **Hydrogenation in crystalline silicon materials for photovoltaic application**  
G. Hahn (*invited*), M. Käs and B. Herzog
- 14:40 – 15:00      **Hydrogen effects in Si substrates for solar cells**  
A. Ulyashin
- 15:00 – 15:20      **EBIC investigation of the influence of hydrogen passivation on thin-film polycrystalline silicon solar cells obtained by aluminium induced crystallization and epitaxy**  
D. Van Gestel, I. Gordon and J. Poortmans
- 15:20 – 15:40      **Influence of hydrogen on the structural stability of annealed ultrathin Si/Ge amorphous layers**  
C. Frigeri, L. Nasi, M. Serényi, A. Csik, Z. Erdélyi and D. L. Beke

15:40 – 16:10

COFFEE BREAK

## Session: Defect Engineering and Gettering

Session chair: D. Yang

16:10 – 16:30

**Iron gettering in CZ silicon during the industrial solar cell process**

A. Laades, K. Lauer, C. Maier, D. Alber, M. Bähr, J. Nutsch, J. Lossen and A. Lawerenz

16:30 – 16:50

**Trans-RP gettering and out-diffusion of oxygen implanted into highly B-doped silicon**

R. Kögler, Ch. Debois, J.W. Gerlach, H. Hutter, A. Mücklich and W. Skorupa

16:50 – 17:10

**Effect of oxygen in low temperature boron and phosphorus diffusion gettering of iron in Czochralski-grown silicon**

V. Vähänissi, A. Haarahiltunen, H. Talvitie, M.I. Asghar, M. Yli-Koski and H. Savin

17:10 – 17:30

**Gettering efficiency of Si (110)/(100) directly bonded hybrid crystal orientation substrates**

T. Aoki, H. Kariyazaki, K. Sueoka and K. Izunome

17:30 – 17:50

**The production of vacancy-oxygen defects in electron-irradiated Cz-Si initially treated at high temperatures and high pressures**

A. Andrianakis, C.A. Londos, A. Misiuk, V.V. Emtsev, G.A. Oganessian and H. Ohyama

18:00 – 19:30

DINNER

## Poster Session 1

19:30 – open end

# Tuesday (September 29, 2009)

## Session: Si-based Photonics and Defect Luminescence

*Session chair: N. Sobolev*

- 08:30 – 09:10      **Silicon periodic structures and their liquid crystal composites**  
E.V. Astrova (*invited*), V.A. Tolmachev, Yu.A. Zharova, G.V. Fedulova,  
A.V. Baldycheva and T.S. Perova
- 09:10 – 09:30      **Dependence of luminescence properties of bonded Si wafers on surface twist angle**  
E.A. Steinman, O. Kononchuk, A.N. Tereshchenko and A.A. Mazilkin
- 09:30 – 09:50      **D-line emission from small angle grain boundaries in multicrystalline Si**  
T. Sekiguchi, W. Lee, J. Chen and B. Chen
- 09:50 – 10:10      **Determination of the origin of dislocation related luminescence from silicon using regular dislocation networks**  
T. Mchedlidze, O. Kononchuk, T. Arguirov, M. Trushin, M. Reiche and M. Kittler
- 10:10 – 10:30      *COFFEE BREAK*

*Session chair: V. Kveder*

- 10:30 – 10:50      **Structural and luminescent properties of implanted silicon layers with dislocation-related luminescence**  
N.A. Sobolev, Kalyadin, R.N. Kyutt, E.I. Shek and V.I. Vdovin
- 10:50 – 11:10      **Optimization of the luminescence properties of silicon diodes produced by implantation and annealing**  
T. Arguirov, T. Mchedlidze, M. Reiche and M. Kittler
- 11:20 – 12:20      *LUNCH*

## Excursion to Berlin

- 12:30                  Departure to excursion
- 19:00                  Expected time of arrival from Berlin
- 19:00 – 20:30      *DINNER*

## Poster Session 2

20:30 – open end

# Wednesday (September 30, 2009)

## Session: Advanced Semiconductor Materials and Devices

Session chair: V. Litovchenko

- 09:10 – 09:50      **Advanced Si-based semiconductors for energy and photonic applications**  
J. Kouvetakis (*invited*), J. Menendez and J. Tolle
- 09:50 – 10:30      **Strained silicon devices**  
M. Reiche (*invited*), O. Mountanabbir, J. Hoentschel, U. Gösele, S. Flachowsky and M. Horstmann
- 10:30 – 10:50      *COFFE BREAK*

Session chair: G. Rozgonyi

- 10:50 – 11:30      **Novel trends in SOI technology for CMOS applications**  
O. Kononchuk (*invited*), D. Landru and C. Veytizou
- 11:30 – 11:50      **Si wafer bonding: Structural features of the interface**  
V.I. Vdovin, N.D. Zakharov, E. Pippel, P. Werner, M.G. Milvidskii, M. Ries, M. Seacrist and R. Falster
- 11:50 – 12:10      **Semi-insulating silicon for microwave devices**  
D.M. Jordan, K. Mallik, R.J. Falster and P.R. Wilshaw
- 12:10 – 14:00      *LUNCH*

## Session: Modeling

Session chair: P. Pichler

- 14:00 – 14:20      **Optimization of silicon ingot quality by the numerical prediction of bulk crystal defects**  
F. Loix, F. Dupret, A. de Potter, R. Rolinsky, N. Van den Bogaert and V. Regnier
- 14:20 – 14:40      **Simulation of iron distribution after crystallization of mc-silicon**  
J. Schön, H. Habenicht, M.C. Schubert and W. Warta
- 14:40 – 15:00      **Modeling of dislocations in Ge/Si nanostructures by finite element method**  
R. Gatti, F. Boioli, A. Marzegalli, F. Montalenti and L. Miglio
- 15:00 – 15:20      **Atomistic simulation of recrystallization of amorphous Si, Ge and SiGe**  
M. Posselt and A. Gabriel

- 15:20 – 15:40      **Ab initio study of hydrogenated defects and platelets models in hydrogen implanted Si**  
L. Billeau, A. Tazuin and J.-P. Crocombette
- 15:40 – 16:00      **Molecular simulation on interfacial structure and gettering efficiency of Si (110)/(100) directly bonded hybrid crystal orientation substrates**  
H. Kariyazaki, T. Aoki, K. Izunome and K. Sueoka
- 16:00 – 16:30                      *COFFEE BREAK*

## **Session: Defect and Impurity Characterization I**

*Session chair: T. Sekiguchi*

- 16:30 – 17:10      **Synchrotron microscopy and spectroscopy for analysis of solar Si**  
W. Seifert (*invited*), O. Vyvenko, T. Arguirov, M. Trushin and M. Kittler
- 17:10 – 17:30      **Quantitative iron concentration imaging**  
M.C. Schubert, H. Habenicht, M.J. Kerler and W. Warta
- 17:30 – 17:50      **Divacancy-oxygen and trivacancy-oxygen complexes in silicon: Local vibrational mode studies**  
L.I. Murin, B.G. Svensson, J.L. Lindström, V.P. Markevich and C.A. Londos
- 18:00 – 19:30                      *DINNER*

## **Poster Session 2**

19:30 – open end



# Thursday (October 01, 2009)

## Session: Impurity Engineering and Radiation-Induced Defects

Session chair: O. Kononchuk

- 09:00 – 09:40      **Can impurities be beneficial to photovoltaics?**  
A. Luque (*invited*) and A. Marí
- 09:40 – 10:20      **Impurity engineering of Czochralski silicon**  
J. Chen, X. Ma and D. Yang (*invited*)
- 10:20 – 10:40      **Role of ion irradiation induced lattice defects on nanoscale capacitive behavior of graphene**  
S. Sonde, F. Giannazzo, V. Raineri, S. Di Franco, A. Marino and E. Rimini
- 10:40 – 11:00      *COFFE BREAK*

Session chair: V. Raineri

- 11:00 – 11:20      **Formation of radiation-induced defects in Si crystals irradiated with electrons at elevated temperatures**  
V.P. Markevich, A.R. Peaker, S.B. Lastovskii, V.E. Gusakov, I.F. Medvedeva and L.I. Murin
- 11:20 – 11:40      **Accumulation of hydrogen within implantation-damaged areas in processed Si:N and Si:O**  
A. Misiuk, A. Ulyashin, A. Barcz and P. Formanek
- 11:40 – 12:00      **Anisotropic strain - Anisotropic heating engineering for Si nanocrystals in SiO<sub>2</sub>**  
I.V. Antonova, D.V. Marin, V.A. Volodin, V.A. Skuratov, J. Jedrzejewski and I. Balberg
- 12:00 – 14:00      *LUNCH*

Session chair: B. Pichaud

- 14:00 – 14:20      **Co-precipitation of copper and nickel in crystalline Si under copper- and nickel- rich conditions**  
C. Rudolf, P. Saring, L. Stolze and M. Seibt
- 14:20 – 14:40      **Radiation defects in silicon: Effect of contamination by platinum atoms**  
P. Hazdra and V. Komarnitskyy

## Session: Defect and Impurity Characterization II

14:40 – 15:20           **Grain boundaries in multicrystalline Si**  
J. Chen (*invited*), B. Chen, W. Lee, M. Fukuzawa, M. Yamada and  
T. Sekiguchi

15:20 – 15:50            *COFFEE BREAK*

*Session chair: L. Fabry*

15:50 – 16:10           **Electronic states of oxygen-free dislocation networks produced  
by direct bonding of silicon wafers**  
M. Trushin, O. Vyvenko, T. Mchedlidze, O. Kononchuk and M. Kittler

16:10 – 16:30           **Correlation study of morphology, electrical activation and contact  
formation of ion implanted 4H-SiC**  
M.H. Weng, F. Roccaforte, F. Giannazzo, S. Di Franco, C. Bongiorno,  
E. Zanetti, A. Ruggiero, M. Saggio and V. Raineri

16:30 – 16:50           **Characterization of semiconductor films epitaxially grown on thin  
metal oxide buffer layers**  
P. Zaumseil, A. Giussani, O. Seifarth, T. Arguirov, A. Schubert and  
T. Schroeder

16:50 – 17:10           **Comparative study of electrical and optical properties of  
plastically deformed Si**  
N. Yarykin and O. Feklisova

19:00 – open end            *CONFERENCE DINNER*

**Friday (October 02, 2009)**

## Session: Nanostructures and Novel Devices

Session chair: P. Wilshaw

- 09:00 – 09:40      **Current status of graphene transistors**  
M.C. Lemme (*invited*)
- 09:40 – 10:00      **Theoretical study of ionized impurities in silicon nanowire MOS transistors**  
M. Bescond, M. Lannoo, L. Raymond and F. Michelini
- 10:00 – 10:20      **Optical properties of Si nanowires catalyzed by arrays of gold nanoparticles with controlled diameters**  
G. Brönstrup, D. Leroose, M.G. Jenke, Ch. Niederberger, J. Hankache, M. Bechelany, L. Philippe, I. Utke, J. Michler and S. Christiansen
- 10:20 – 10:40                      *COFFEE BREAK*

Session chair: A. Luque

- 10:40 – 11:20      **Clean energy: The case for thermoelectrics and photovoltaics**  
A. Boukai (*invited*)
- 11:20 – 11:40      **Axial heterojunctions in Si nanowires by Pulsed Laser Deposition: Doping and Si/Ge layer stacks**  
B. Eisenhawer, A. Berger, D. Zhang, J. Michler and S. Christiansen
- 11:40 – 11:50      Closing Remarks
- 12:00 – 13:00                      *LUNCH*
- 13:00                      Bus departure to Berlin

# POSTER SESSION 1 (Sunday and Monday)

## Photovoltaic Silicon

- P1 Growth of silicon carbide filaments in multicrystalline silicon for solar cells**  
H.J. Möller, C. Funke, J. Bauer, S. Köstner, H. Straube and O. Breitenstein
- P2 Analysis of silicon carbide and silicon nitride precipitates in block cast multicrystalline silicon**  
M. Holla, T. Arguirov, W. Seifert and M. Kittler
- P3 Investigations on the behaviour of carbon during inductive melting of multicrystalline silicon**  
L. Raabe, J. Ehrig, S. Würzner, O. Pätzold, M. Stelter and H.J. Möller
- P4 An investigation into fracture of multi-crystalline silicon**  
B.R. Mansfield, D.E.J. Armstrong, P.R. Wilshaw and J.D. Murphy
- P5 Hydrogen-induced passivation of grain-boundary defects in polycrystalline silicon**  
N.H. Nickel
- P6 Bulk passivation of defects in multi-crystalline silicon solar cells by a-SiN<sub>x</sub>:H layers**  
E. Cornagliotti, H.F.W. Dekkers, C. Prastani, J. John, E. Van Kerschaver, J. Poortmans and R.P. Mertens
- P7 Passivation of Si surfaces investigated by in-situ photoluminescence techniques**  
J. Rappich, X. Zhang, D.M. Rosu, U. Schade and K. Hinrichs
- P8 Study of internal versus external gettering of iron during slow cooling processes for silicon solar cell fabrication**  
J. Hofstetter, J.-F. Lelièvre, C. del Cañizo and A. Luque
- P9 Characterization of thin film photovoltaic material using photoluminescence and Raman spectroscopy**  
T. Mchedlidze, T. Arguirov, S. Kouteva-Arguirova and M. Kittler
- P10 Epitaxial film silicon solar cells by hot wire chemical vapor deposition below 750 C**  
K. Alberi, I.T. Martin, C.W. Teplin, E. Iwaniczko, Y. Xu, A. Duda, P. Stradins, S.W. Johnston, H.R. Moutinho, H.M. Branz and D.L. Young
- P11 3rd generation solar cell prototype based on chemically formed silicon nanowires: Processing, optical and photovoltaic properties**  
V.A. Sivakov, G. Brönstrup, A. Gawlik, A. Berger and S.H. Christiansen
- P12 SEM characterization of silicon layers grown on carbon foil**  
S.K. Brantov, A.V. Eltzov, O.V. Feklisova and E.B. Yakimov
- P13 An express method for the study of planar homogeneity of diffusion length in multicrystalline solar silicon**

## Defect Aspects and Gettering

- P14 Anomalous out-diffusion profiles of nitrogen in silicon**  
V.V. Voronkov, R. Falster and S. Senkader
- P15 Growth of heavily phosphorus-doped (111) silicon crystals**  
F. Liu, H.P. Han, Y.M. Wang and L.Y. Tong
- P16 Study of the mechanisms of oxygen precipitation in RTA annealed Cz-Si wafers**  
V. Litovchenko, I. Lisovskyy, M. Voitovych, A. Sarikov, S. Zlobin, V. Kladko and V. Machulin
- P17 Dislocation states and deformation-induced point defects in plastically deformed germanium**  
S. Shevchenko and A. Tereshchenko
- P18 Defect generation during plastic deformation of Si-rich Cz-grown SiGe crystals**  
N. Yarykin and N.V. Abrosimov
- P19 Boron and phosphorus implantation induced electrically active defects in p-type silicon**  
J. Senawiratne, J.S. Cites, J.G. Couillard, J. Moll, C.A. Kosik Williams and P.G. Whiting
- P20 Suppression of pores formation on a surface of p-Si by laser radiation**  
A. Medvid, P. Onufrijevs, L. Fedorenko, N.Yusupov and E. Daukšta
- P21 Far-action defects formation and gettering in 6H-SiC Lely crystals irradiated by Bi**  
D.B. Shustov, E.V. Kolesnikova, E.V. Kalinina, V.A. Skuratov and M.V. Zamoryanskaya
- P22 Evaluation criteria for efficient gettering applied for Cu and Ni impurities in Si wafers**  
D. Kot, G. Kissinger, M. A. Schubert, A. Sattler and W. von Ammon
- P23 Aluminum gettering of iron in silicon**  
D. Abdelbarey, V. V. Kveder, W. Schröter and M. Seibt
- P24 Spatially resolved defect analysis in Cz-silicon after copper-nickel co-precipitation by virtue of light-beam-induced current measurements**  
P. Saring, C. Rudolf, L. Stolze, A. Falkenberg and M. Seibt

## Defect Aspects, Characterization and Modeling

- P25 Delineation of microdefects in silicon substrates by chromium-free preferential etching solutions and laser scattering tomography**  
M. Pellowska, D. Possner, D. Kot, G. Kissinger and B.O. Kolbesen
- P26 Vacancies and self-interstitials dynamics in silicon wafers**  
O. Caha, J. Kubena, A. Kubena and M. Meduna
- P27 Interaction of point defects with impurities in the Si-SiO<sub>2</sub> system and its influence on the properties of the interface**  
D. Kropman, E. Mellikov, K. Lott, T. Kärner, I. Heinmaa, T. Laas, A. Medvid, W. Skorupa, S. Prucnal, S. Zvyagin, E. Cizmar, M. Ozerov and J. Woznitsa
- P28 DLTS studies of carbon related complexes in irradiated n- and p-silicon**  
L.F. Makarenko, F.P. Korshunov, S.B. Lastovski, L.I. Murin and M. Moll
- P29 The effect of germanium doping on the production of carbon-related defects in electron-irradiated Czochralski silicon**  
C.A. Londos, A. Andrianakis, D. Aliprantis, E. Sgourou, V.V. Emtsev and H. Ohyama
- P30 Formation of radiation hardened SOI structures by N<sup>+</sup> implantation in SiO<sub>2</sub> film and subsequent hydrogen transfer of Si layer**  
I.E. Tyschenko and V.P. Popov  
presented by I.V. Antonova
- P31 Onset of blistering in low-dose hydrogen implanted and then hydrogen plasma treated Si: Formation of porous-like structures and layer exfoliation processes**  
A. Ulyashin, H. Nordmark, A. Misiuk, J. C. Walmsley and R. Holmestad
- P32 Thermal optimization of Cz silicon single crystal growth**  
A.I. Prostromolotov, N.A. Verezub and M.G. Milvidskii
- P33 Comparison of efficiency and kinetics of phosphorus-diffusion and aluminum gettering of metal impurities in silicon: A simulation study**  
M.A. Falkenberg, D. Abdelbarey, V.V. Kveder and M. Seibt
- P 34 Atomistic simulations of point defect diffusion in Si and SiGe: A powerful tool for point defect engineering**  
P. Pochet, D. Caliste, K. Rushchanskii, F. Lancon and T. Deutsch
- P35 Effect of growth conditions and catalyst material on nanowisker morphology: Monte Carlo simulation**  
A.G. Nastovjak, I.G. Neizvestny and N.L. Schwartz  
presented by I.V. Antonova
- P36 Versatile simulation tool and novel measurement method for electrical characterization of semiconductors**  
N. Schüler, T. Hahn, K. Dornich and J.R. Niklas
- P37 Simulation of XBIC contrast of precipitates in Si**  
E.B. Yakimov

- P38 Oxygen trimer in silicon: an infrared absorption study**  
L.I. Murin, V.P. Markevich, B.G. Svensson and J.L. Lindström
- P39 In-situ observation of oxygen precipitation in silicon with high energy X-rays**  
H. Grillenberger and A. Magerl
- P40 Electron-beam-induced current study of breakdown behavior of high-k gate MOSFETs**  
J. Chen, T. Sekiguchi, M. Takase, N. Fukata, R. Hasunuma, K. Yamabe, M. Sato, K. Yamada and T. Chikyo
- P41 Investigation of the mechanical properties of thin films by bulge test**  
A. Hémel, T. Schenk, A. Jacques and T. Kruml
- P42 Defect characterization of poly-Ge and VGF-grown Ge material**  
M. Holla, T. Arguirov, G. Jia, M. Kittler, Ch. Frank-Rotsch, F. Kiessling and P. Rudolph

## Nanostructures

- P43 Scaling in quantum transport in silicon nano-transistors**  
U. Wulf and H. Richter
- P44 Silicon cluster aggregation in silica layers**  
H.-J. Fitting, L. Fitting-Kourkoutis, R. Salh, E.V. Kolesnikova, M.V. Zamoryanskaya and B. Schmidt
- P45 Feedback effect on the self-organized nanostructures formation on silicon upon femtosecond laser ablation**  
O. Varlamova, M. Ratzke and J. Reif
- P46 Confinement levels in passivated SiGe/Si quantum well structures**  
I.V. Antonova, E.P. Neustroev, S.A. Smagulova, M.S. Kagan, P.S. Alekseev, S.K. Ray, N. Sustersic and J. Kolodzey
- P47 Structural transformations in Si nanostructures induced by swift heavy ions**  
G.A. Kachurin, S.G. Cherkova, D.V. Marin, A.G. Cherkov and V.A. Skuratov  
presented by I.V. Antonova
- P48 Impurity doping of Si nanowires synthesized by laser**  
N. Fukata, M. Seoka, N. Saito, K. Sato, J. Chen, T. Sekiguchi and K. Murakami